



SANYO Semiconductors

## DATA SHEET

CPH5852

MOSFET : P-Channel Silicon MOSFET

SBD : Schottky Barrier Diode

## General-Purpose Switching Device Applications

### Features

- Composite type containing a P-Channel MOSFET (MCH3312) and a Schottky Barrier Diode (SB1003M3), facilitating high-density mounting.
- [MOS]
  - Low ON-resistance
  - Ultrahigh-speed switching
  - 4V drive
- [SBD]
  - Short reverse recovery time
  - Low forward voltage

### Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
[MOSFET]				
Drain-to-Source Voltage	V <sub>DSS</sub>		-30	V
Gate-to-Source Voltage	V <sub>GSS</sub>		±20	V
Drain Current (DC)	I <sub>D</sub>		-2	A
Drain Current (Pulse)	I <sub>DP</sub>	PW≤10μs, duty cycle≤1%	-8	A
Allowable Power Dissipation	P <sub>D</sub>	Mounted on a ceramic board (600mm <sup>2</sup> X0.8mm) 1unit	0.9	W
Channel Temperature	T <sub>ch</sub>		150	°C
Storage Temperature	T <sub>stg</sub>		-55 to +125	°C
[SBD]				
Repetitive Peak Reverse Voltage	V <sub>R</sub> RM		30	V
Nonrepetitive Peak Reverse Surge Voltage	V <sub>R</sub> SM		35	V
Average Output Current	I <sub>O</sub>		1	A
Surge Forward Current	I <sub>FSM</sub>	50Hz sine wave, 1cycle	10	A
Junction Temperature	T <sub>J</sub>		-55 to +125	°C
Storage Temperature	T <sub>stg</sub>		-55 to +125	°C

Marking : YE

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**SANYO Semiconductor Co., Ltd.**

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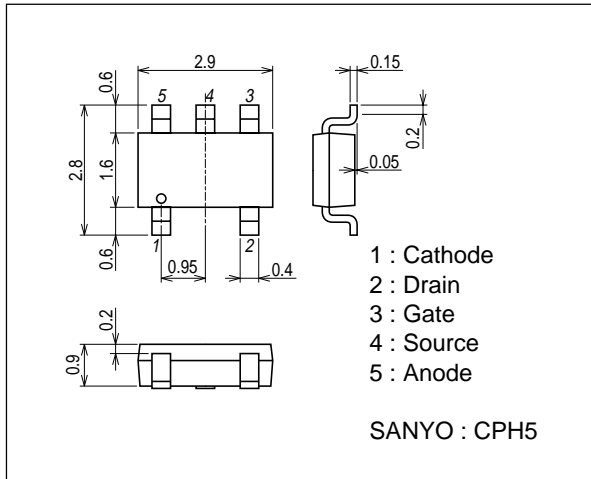
# CPH5852

## Electrical Characteristics at Ta=25°C

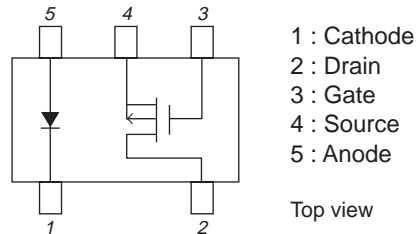
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
[MOSFET]						
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D=-1mA, V_{GS}=0V$	-30			V
Zero-Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=-30V, V_{GS}=0V$			-1	$\mu A$
Gate-to-Source Leakage Current	$I_{GSS}$	$V_{GS}=\pm 16V, V_{DS}=0V$			$\pm 10$	$\mu A$
Cutoff Voltage	$V_{GS(off)}$	$V_{DS}=-10V, I_D=-1mA$	-1.2		-2.6	V
Forward Transfer Admittance	$ y_{fs} $	$V_{DS}=-10V, I_D=-1A$	1.2	2.0		S
Static Drain-to-Source On-State Resistance	$R_{DS(on)1}$	$I_D=-1A, V_{GS}=-10V$		110	145	$m\Omega$
	$R_{DS(on)2}$	$I_D=-500mA, V_{GS}=-4V$		205	290	$m\Omega$
Input Capacitance	$C_{iss}$	$V_{DS}=-10V, f=1MHz$		200		pF
Output Capacitance	$C_{oss}$	$V_{DS}=-10V, f=1MHz$		47		pF
Reverse Transfer Capacitance	$C_{rss}$	$V_{DS}=-10V, f=1MHz$		32		pF
Turn-ON Delay Time	$t_{d(on)}$	See specified Test Circuit.		7.2		ns
Rise Time	$t_r$	See specified Test Circuit.		2.9		ns
Turn-OFF Delay Time	$t_{d(off)}$	See specified Test Circuit.		21		ns
Fall Time	$t_f$	See specified Test Circuit.		8.7		ns
Total Gate Charge	$Q_g$	$V_{DS}=-10V, V_{GS}=-10V, I_D=-2A$		5.5		nC
Gate-to-Source Charge	$Q_{gs}$	$V_{DS}=-10V, V_{GS}=-10V, I_D=-2A$		0.98		nC
Gate-to-Drain "Miller" Charge	$Q_{gd}$	$V_{DS}=-10V, V_{GS}=-10V, I_D=-2A$		0.82		nC
Diode Forward Voltage	$V_{SD}$	$I_S=-2A, V_{GS}=0V$		-0.85	-1.2	V
[SBD]						
Reverse Voltage	$V_R$	$I_R=0.5mA$	30			V
Forward Voltage	$V_{F1}$	$I_F=0.7A$		0.45	0.5	V
	$V_{F2}$	$I_F=1.0A$		0.48	0.53	V
Reverse Current	$I_R$	$V_R=16V$			15	$\mu A$
Interterminal Capacitance	$C$	$V_R=10V, f=1MHz$ cycle		27		pF
Reverse Recovery Time	$t_{rr}$	$I_F=I_R=100mA$ , See specified Test Circuit.			10	ns

### Package Dimensions

unit : mmm  
7017A-005

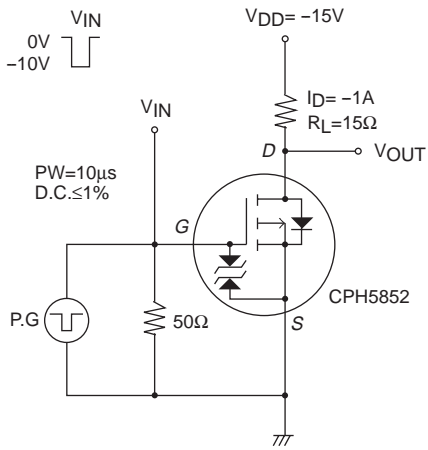


### Electrical Connection



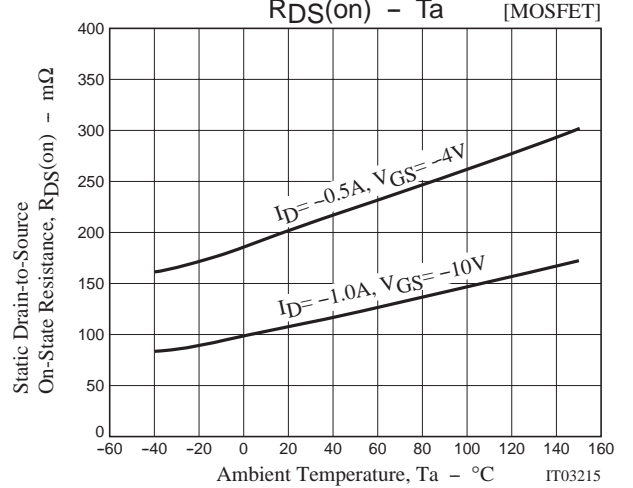
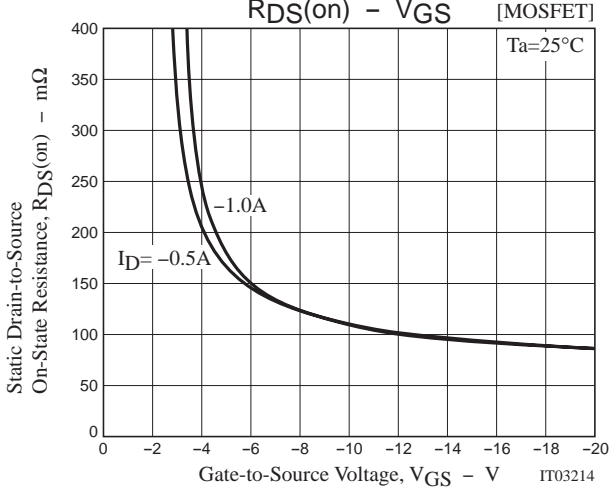
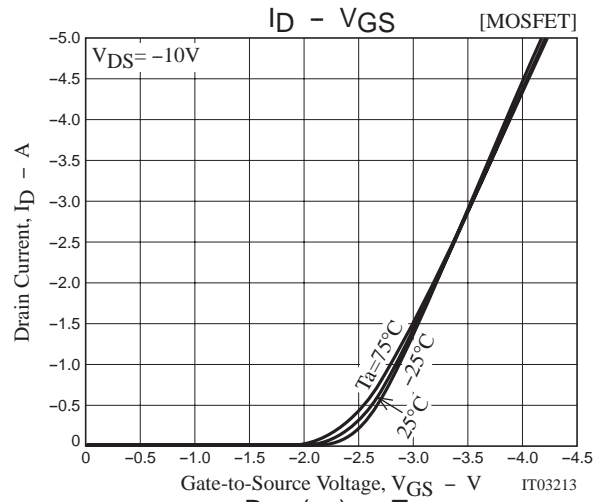
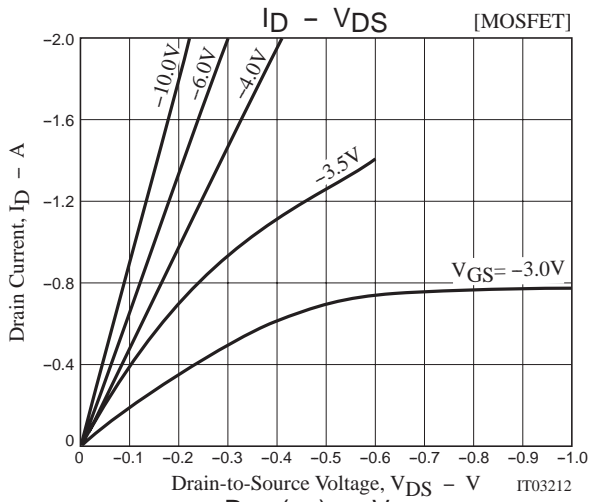
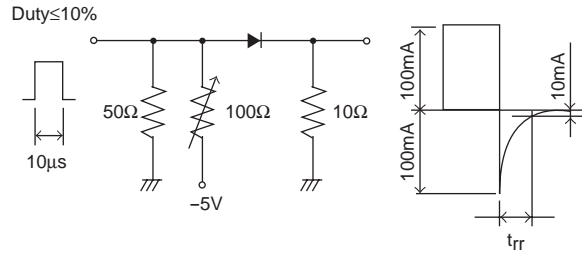
Switching Time Test Circuit

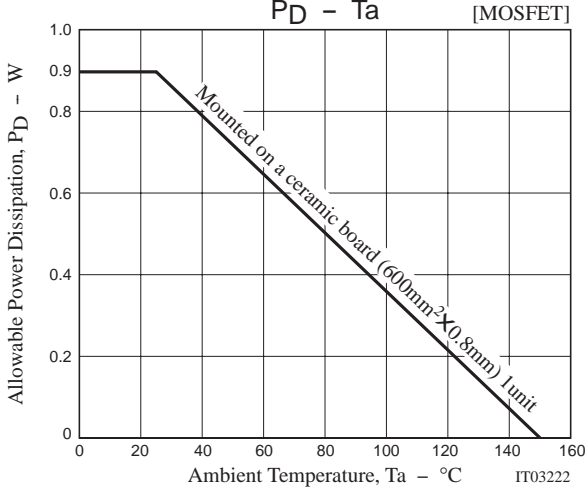
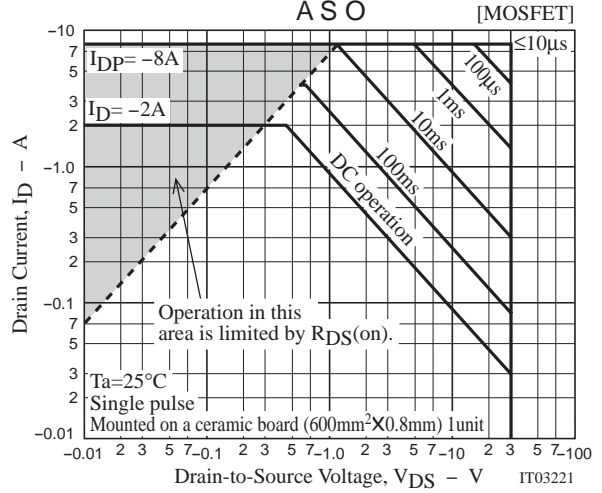
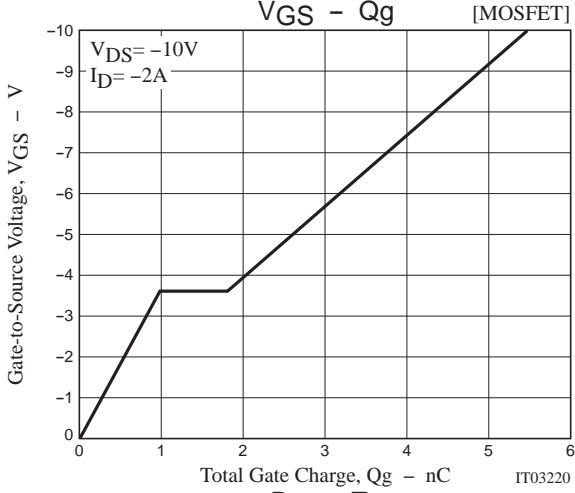
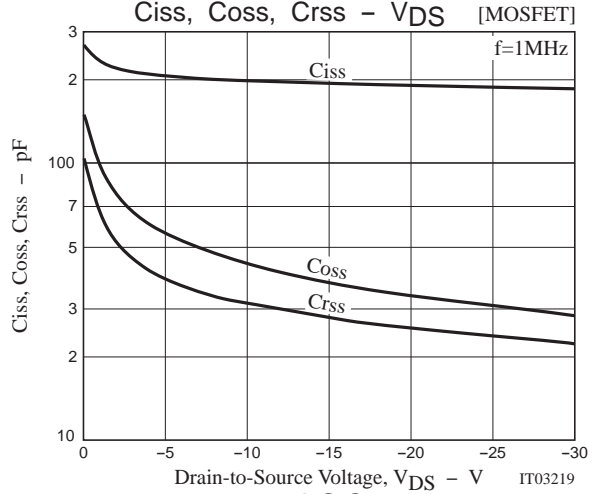
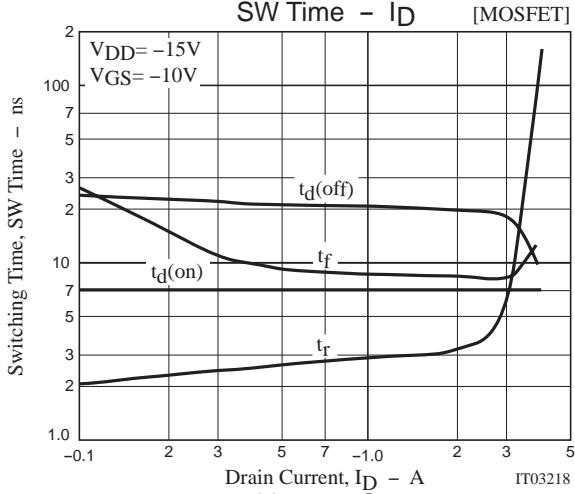
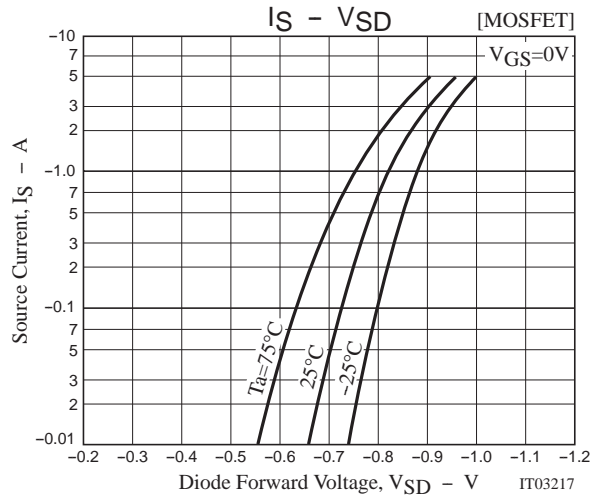
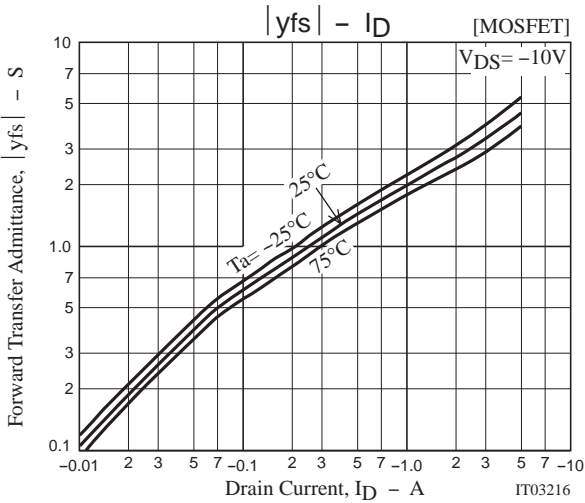
[MOSFET]

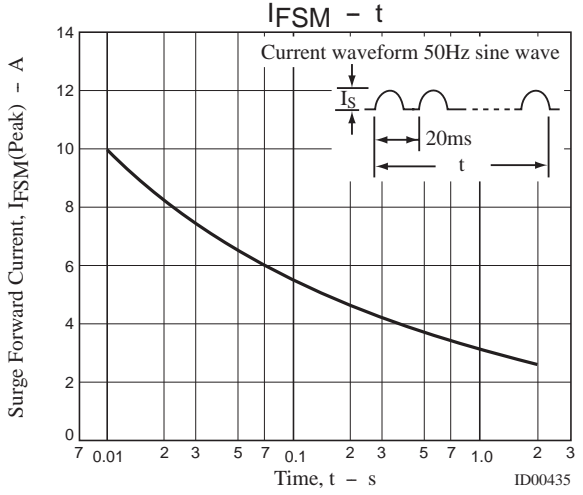
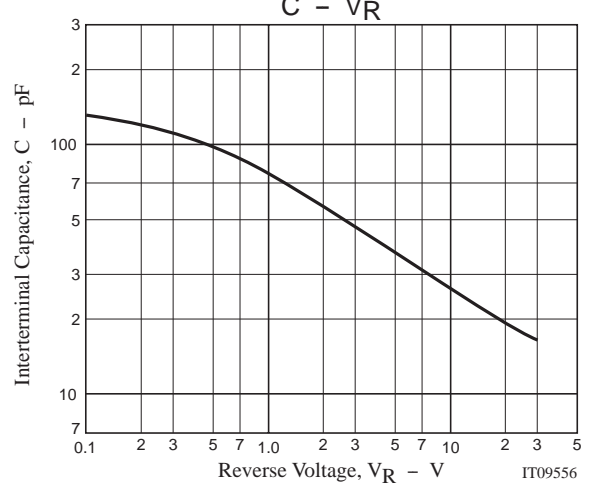
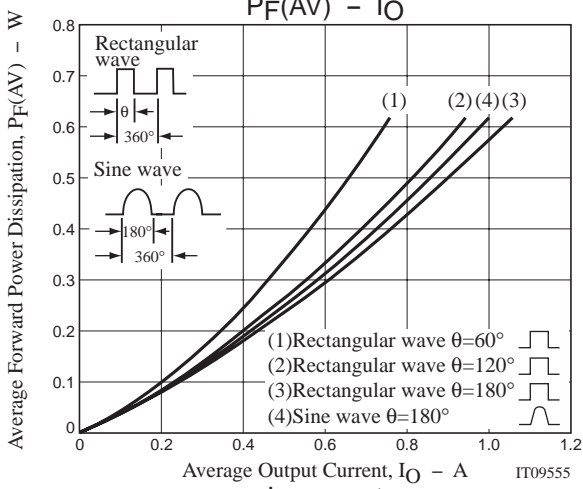
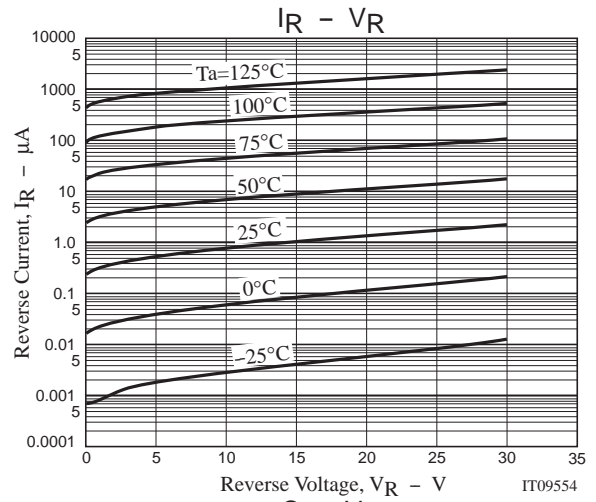
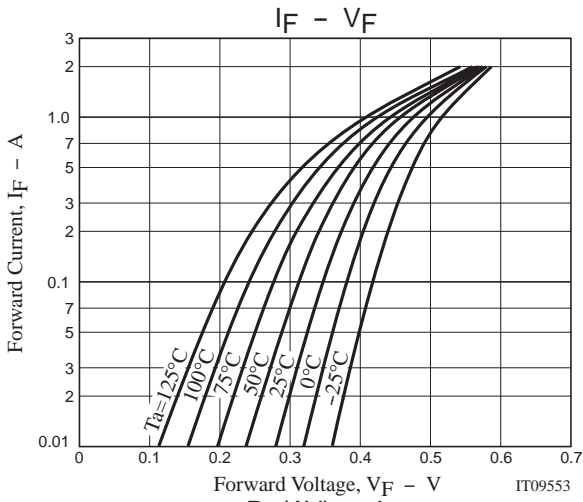


$t_{rr}$  Test Circuit

[SBD]







Note on usage : Since the CPH5852 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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